RENESAS FemtoClock[®] Crystal-to-LVDS

Frequency Synthesizer

844002

GENERAL DESCRIPTION

The 844002 is a 2 output LVDS Synthesizer optimized to generate Fibre Channel reference clock frequencies. Using a 26.5625MHz 18pF parallel resonant crystal, the following frequencies can be generated based on the 2 frequency select pins (F_SEL[1:0]): 212.5MHz, 187.5MHz, 159.375MHz, 106.25MHz and 53.125MHz. The 844002 uses IDT's 3rd generation low phase noise VCO technology and can achieve <1ps typical rms phase jitter, easily meeting Fibre Channel jitter requirements. The 844002 is packaged in a small 20-pin TSSOP package.

FEATURES

- · Two LVDS outputs
- Selectable crystal oscillator interface or LVCMOS/LVTTL single-ended input
- Supports the following output frequencies: 212.5MHz, 187.5MHz, 159.375MHz, 106.25MHz and 53.125MHz
- VCO range: 560MHz 680MHz
- RMS phase jitter @ 212.5MHz, using a 26.5625MHz crystal (637kHz - 10MHz): 0.65ps (typical)
- Full 3.3V or 2.5V supply modes
- 0°C to 70°C ambient operating temperature
- Available in lead-free (RoHS 6) package

FREQUENCY SELECT FUNCTION TABLE

		In	puts			Output
Input Frequency (MHz)	F_SEL1	F_SEL0	M Divider Value	N Divider Value	M/N Divider Value	Frequency (MHz)
26.5625	0	0	24	3	8	212.5 (default)
26.5625	0	1	24	4	6	159.375
26.5625	1	0	24	6	4	106.25
26.5625	1	1	24	12	2	53.125
23.4375	0	0	24	3	8	187.5 (default)

PIN ASSIGNMENT

nc 🗆	1	20	VDDO
VDDO _	2	19	Q1
Q0 🗖	3	18	nQ1
nQ0 🗆	4	17	GND
MR 🗆	5	16	nc
nPLL_SEL	6	15	nXTAL_SEL
nc 🗆	7	14	REF_CLK
VDDA 🗆	8	13	XTAL_IN
F_SEL0	9	12	XTAL_OUT
VDD 🗆	10	11	F_SEL1

844002 20-Lead TSSOP 6.5mm x 4.4mm x 0.925mm package body **G** Package **Top View**

BLOCK DIAGRAM

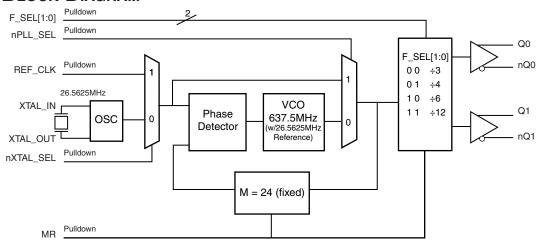




TABLE 1. PIN DESCRIPTIONS

Number	Name	Ту	/ре	Description
1, 7	nc	Unused		No connect.
2, 20	V	Power		Output supply pins.
3, 4	Q0, nQ0	Ouput		Differential output pair. LVDS interface levels.
5	MR	Input	Pulldown	Active HIGH Master Reset. When logic HIGH, the internal dividers are reset causing the true outputs Qx to go low and the inverted outputs nQx to go high. When logic LOW, the internal dividers and the outputs are enabled. LVCMOS/LVTTL interface levels.
6	nPLL_SEL	Input	Pulldown	Selects between the PLL and REF_CLK as input to the dividers. When LOW, selects PLL (PLL Enable). When HIGH, deselects the reference clock (PLL Bypass). LVCMOS/LVTTL interface levels.
8	V	Power		Analog supply pin.
9, 11	F_SEL0, F_SEL1	Input	Pulldown	Frequency select pins. LVCMOS/LVTTL interface levels.
10	V	Power		Core supply pins.
12, 13	XTAL_OUT, XTAL_IN	Input		Parallel resonant crystal interface. XTAL_OUT is the output, XTAL_IN is the input.
14	REF_CLK	Input	Pulldown	LVCMOS/LVTTL reference clock input.
15	nXTAL_SEL	Input	Pulldown	Selects between crystal or REF_CLK inputs as the the PLL Reference source. Selects XTAL inputs when LOW. Selects REF_CLK when HIGH. LVCMOS/LVTTL interface levels.
16	nc	Unused		No connect.
17	GND	Power		Power supply ground.
18, 19	nQ1, Q1	Output		Differential output pair. LVDS interface levels.

NOTE: refers to internal input resistors. See Table 2, Pin Characteristics, for typical values.

TABLE 2. PIN CHARACTERISTICS

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C	Input Capacitance			4		pF
	Input Pulldown Resistor			51		kΩ

RENESAS

ABSOLUTE MAXIMUM RATINGS

Supply Voltage, $V_{_{DD}}$	4.6V
Inputs, V	-0.5V to V_{DD} + 0.5V
Outputs, I Continuous Current Surge Current	10mA 15mA
Package Thermal Impedance, $\boldsymbol{\theta}_{_{\!$	73.2°C/W (0 lfpm)
Storage Temperature, T_{stg}	-65°C to 150°C

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Table 3A. Power Supply DC Characteristics, $V_{dd} = V_{dd} = 3.3V \pm 5\%$, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V	Core Supply Voltage		3.135	3.3	3.465	V
V	Analog Supply Voltage		V _{DD} -0.12	3.3	V	V
V	Output Supply Voltage		3.135	3.3	3.465	V
	Power Supply Current				105	mA
	Analog Supply Current				12	mA
I DDO	Output Supply Current				120	mA

TABLE 3B. Power Supply DC Characteristics, $V_{DD} = V_{DDD} = 2.5V \pm 5\%$, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
	Core Supply Voltage		2.375	2.5	2.625	V
V	Analog Supply Voltage		V _{DD} -0.10	2.5	V	V
V	Output Supply Voltage		2.375	2.5	2.625	V
	Power Supply Current				95	mA
I DDA	Analog Supply Current				10	mA
	Output Supply Current				90	mA

TABLE 3C. LVCMOS / LVTTL DC Characteristics, $V_{DD} = V_{DD0} = 3.3V \pm 5\%$ or 2.5V±5%, Ta = 0°C to 70°C

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V	In most I Rink Malta an		$V_{_{DD}} = 3.3V$	2		V _{DD} + 0.3	V
V _{IH}	Input High Vol	lage	$V_{DD} = 2.5V$	1.7		V _{DD} + 0.3	V
V	Input Low Voltage		$V_{dD} = 3.3V$	-0.3		0.8	V
V			$V_{DD} = 2.5V$	-0.3		0.7	V
I _{III}	Input High Current	REF_CLK, MR, F_SEL0, F_SEL1, nPLL_SEL, nXTAL_SEL,	$V_{DD} = V_{N} = 3.465$ or 2.5V			150	μA
I _{IL}	Input Low Current	REF_CLK, MR, F_SEL0, F_SEL1, nPLL_SEL, nXTAL_SEL,	$V_{_{DD}} = 3.465V \text{ or } 2.5V,$ $V_{_{IN}} = 0V$	-150			μA

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V	Differential Output Voltage		300	450	600	mV
$\Delta V_{_{OD}}$	$V_{_{OD}}$ Magnitude Change				50	mV
V _{os}	Offset Voltage		1.4	1.525	1.65	V
ΔV_{os}	V _{os} Magnitude Change				50	mV

Table 3D. LVDS DC Characteristics, $V_{_{DD}} = V_{_{DDO}} = 3.3V \pm 5\%$, Ta = 0°C to 70°C

Table 3E. LVDS DC Characteristics, $V_{_{DD}} = V_{_{DDO}} = 2.5V \pm 5\%$, Ta = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V	Differential Output Voltage		250	400	550	mV
$\Delta V_{_{OD}}$	$V_{_{OD}}$ Magnitude Change				50	mV
V _{os}	Offset Voltage		1.0		1.4	V
ΔV_{os}	V _{os} Magnitude Change				50	mV

TABLE 4. CRYSTAL CHARACTERISTICS

Parameter	Test Conditions	Minimum	Typical	Maximum	Units
Mode of Oscillation		Fundamental			
Frequency		23.33	26.5625	28.33	MHz
Equivalent Series Resistance (ESR)				50	Ω
Shunt Capacitance				7	pF
Drive Level				1	mW

NOTE: Characterized using an 18pF parallel resonant crystal.

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
f _{оит}		F_SEL[1:0] = 00	186.67		226.66	MHz
	Output Frequency	F_SEL[1:0] = 01	140		170	MHz
	Calput Frequency	F_SEL[1:0] = 10	93.33		113.33	MHz
		F_SEL[1:0] = 11	46.67		56.66	MHz
tsk(o)	Output Skew; NOTE 1, 2				15	ps
		212.5MHz, (637kHz - 10MHz)		0.65		ps
		159.375MHz, (637kHz - 10MHz)		0.61		ps
tjit(Ø)	RMS Phase Jitter (Random); NOTE 3	106.25MHz, (637kHz -10MHz)		0.74		ps
	NOTES	53.125MHz, (637kHz - 10MHz)		0.64		ps
		187.5MHz, (637kHz - 10MHz)		0.80		ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	250		500	ps
		F_SEL[1:0] ≠ ÷3	48		52	%
odc	Output Duty Cycle	F_SEL[1:0] = ÷3	45		55	%

Table 5A. AC Characteristics, $V_{DD} = V_{DDD} = 3.3V \pm 5\%$, TA = 0°C to 70°C

NOTE 1: Defined as skew between outputs at the same supply voltages and with equal load conditions. Measured at the differential cross points.

NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Please refer to the Phase Noise Plot.

Table 5B. AC Characteristics, $V_{_{DD}} = V_{_{DDO}} = 2.5V \pm 5\%$, TA = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
	Output Frequency	F_SEL[1:0] = 00	186.67		226.66	MHz
f		F_SEL[1:0] = 01	140		170	MHz
OUT		F_SEL[1:0] = 10	93.33		113.33	MHz
		F_SEL[1:0] = 11	46.67		56.66	MHz
tsk(o)	Output Skew; NOTE 1, 2				15	ps
tjit(Ø)	RMS Phase Jitter (Random); NOTE 3	212.5MHz, (637kHz - 10MHz)		0.65		ps
		159.375MHz, (637kHz - 10MHz)		0.61		ps
		106.25MHz, (637kHz -10MHz)		0.74		ps
		53.125MHz, (637kHz - 10MHz)		0.64		ps
		187.5MHz, (637kHz - 10MHz)		0.80		ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	250		500	ps
	Output Duty Cycle	F_SEL[1:0] ≠ ÷3	48		52	%
odc		F_SEL[1:0] = ÷3	45		55	%

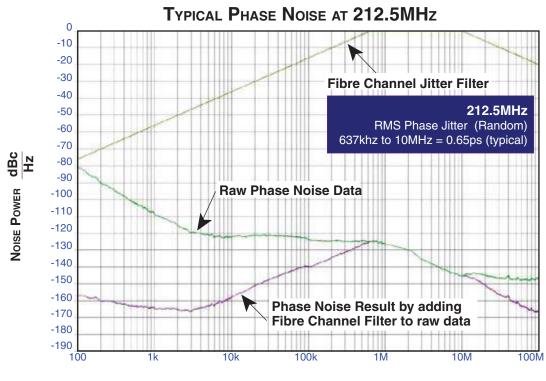
NOTE 1: Defined as skew between outputs at the same supply voltages and with equal load conditions.

Measured at the differential cross points.

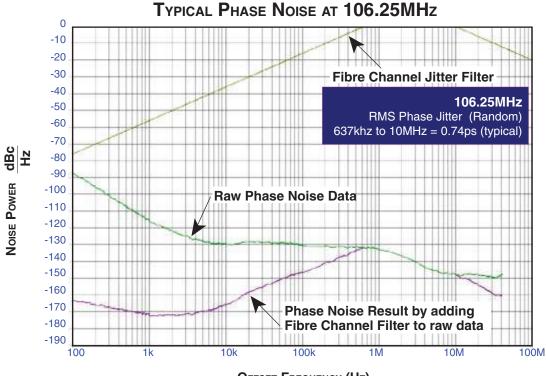
NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 3: Please refer to the Phase Noise Plot.

RENESAS

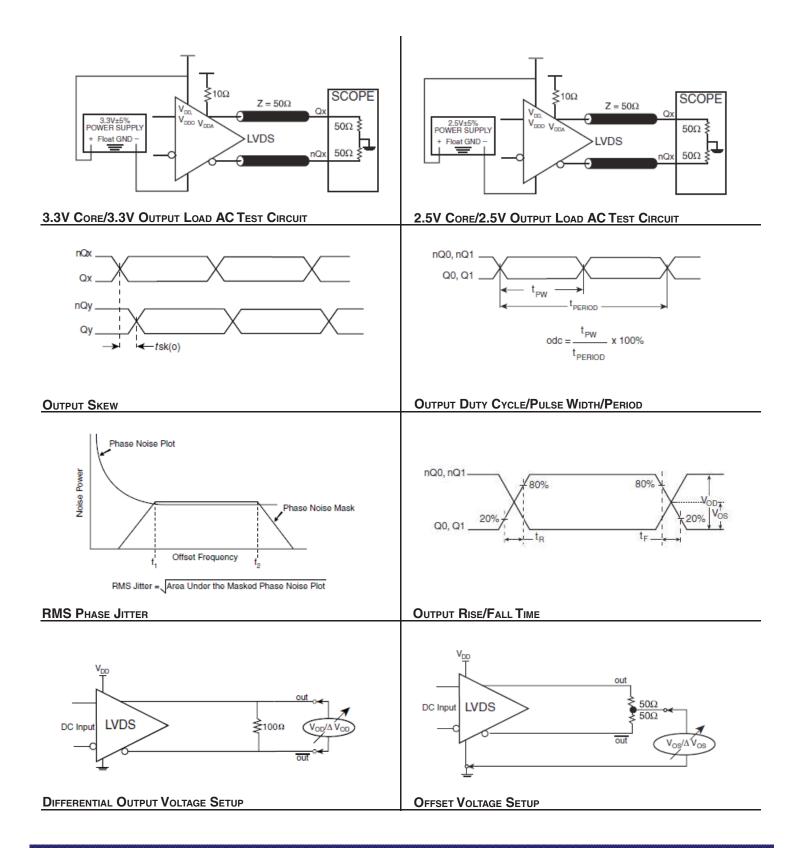


OFFSET FREQUENCY (Hz)



OFFSET FREQUENCY (Hz)

PARAMETER MEASUREMENT INFORMATION



APPLICATION INFORMATION

Power Supply Filtering Techniques

As in any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The 844002 provides separate power supplies to isolate any high switching noise from the outputs to the internal PLL. $V_{_{DD}}$, $V_{_{DDA}}$ and $V_{_{DDO}}$ should be individually connected to the power supply plane through vias, and 0.01µF bypass capacitors should be used for each pin. *Figure 1* illustrates this for a generic $V_{_{CC}}$ pin and also shows that $V_{_{DDA}}$ requires that an additional10 Ω resistor along with a 10µF bypass capacitor be connected to the $V_{_{DDA}}$ pin.

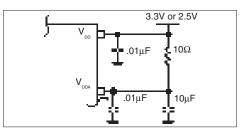


FIGURE 1. POWER SUPPLY FILTERING

CRYSTAL INPUT INTERFACE

The 844002 has been characterized with 18pF parallel resonant crystals. The capacitor values shown in *Figure 2* below

were determined using a 26.5625MHz, 18pF parallel resonant crystal and were chosen to minimize the ppm error.

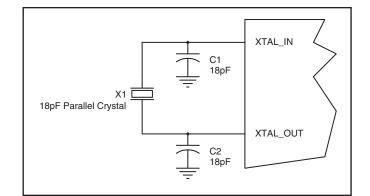


FIGURE 2. CRYSTAL INPUT INTERFACE



LVCMOS TO XTAL INTERFACE

The XTAL_IN input can accept a single-ended LVCMOS signal through an AC coupling capacitor. A general interface diagram is shown in *Figure 3*. The XTAL_OUT pin can be left floating. The input edge rate can be as slow as 10ns. For LVCMOS inputs, it is recommended that the amplitude be reduced from full swing to half swing in order to prevent signal interference with the power rail and to reduce noise. This configuration requires that the output

impedance of the driver (Ro) plus the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be done in one of two ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most 50 Ω applications, R1 and R2 can be 100 Ω . This can also be accomplished by removing R1 and making R2 50 Ω .

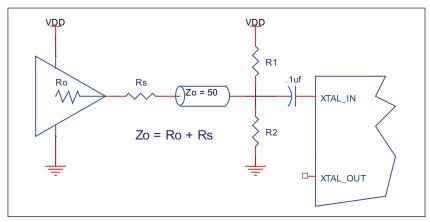


FIGURE 3. GENERAL DIAGRAM FOR LVCMOS DRIVER TO XTAL INPUT INTERFACE

RECOMMENDATIONS FOR UNUSED INPUT AND OUTPUT PINS

NPUTS:

CRYSTAL INPUTS

For applications not requiring the use of the crystal oscillator input, both XTAL_IN and XTAL_OUT can be left floating. Though not required, but for additional protection, a $1k\Omega$ resistor can be tied from XTAL_IN to ground.

REF_CLK INPUT

For applications not requiring the use of the reference clock, it can be left floating. Though not required, but for additional protection, a $1k\Omega$ resistor can be tied from the REF_CLK to ground.

LVCMOS CONTROL PINS

All control pins have internal pulldowns; additional resistance is not required but can be added for additional protection. A 1k Ω resistor can be used.

OUTPUTS:

LVDS OUTPUTS

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, we recommend that there is no trace attached.



3.3V, 2.5V LVDS DRIVER TERMINATION

A general LVDS interface is shown in *Figure 4*. In a 100Ω differential transmission line environment, LVDS drivers require a matched load termination of 100Ω across near

the receiver input. For a multiple LVDS outputs buffer, if only partial outputs are used, it is recommended to terminate the unused outputs.

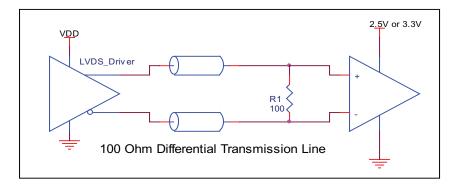


FIGURE 4. TYPICAL LVDS DRIVER TERMINATION

Power Considerations

This section provides information on power dissipation and junction temperature for the 844002. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the 844002 is the sum of the core power plus the power dissipated in the load(s). The following is the power dissipation for $V_{nn} = 3.3V + 5\% = 3.465V$, which gives worst case results.

- Power (core)_{MAX} = V_{DD,MAX} * (I_{DD,MAX} + I_{DDA,MAX}) = 3.465V * (105mA + 12mA) = 405.4mW
- Power (outputs)_{MAX} = V_{DD0_MAX} * I_{DD0_MAX} = 3.465V * 120mA = 415.8mW

Total Power ____ = 405.4mW + 415.8mW = 821.2mW

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad and directly affects the reliability of the device. The maximum recommended junction temperature for HiPerClockS[™] devices is 125°C.

The equation for Tj is as follows: Tj = $\theta_{JA} * Pd_{total} + T_A$

Tj = Junction Temperature

q_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming a moderate air flow of 200 linear feet per minute and a multi-layer board, the appropriate value is 66.6°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 70°C with all outputs switching is: $70^{\circ}C + 0.821W + 66.6^{\circ}C/W = 124.6^{\circ}C$. This is below the limit of $125^{\circ}C$.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow, and the type of board (single layer or multi-layer).

TABLE 6. THERMAL RESISTANCE θ_{JA} for 20-Lead TSSOP, Forced Convection

θ _{JA} by Velocity (Li		initic)	
	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	114.5°C/W	98.0°C/W	88.0°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	73.2°C/W	66.6°C/W	63.5°C/W

RELIABILITY INFORMATION

TABLE 7. $\boldsymbol{\theta}_{_{JA}} \text{vs.}$ Air Flow Table for 20 Lead TSSOP

	0	200	500
Single-Layer PCB, JEDEC Standard Test Boards	114.5°C/W	98.0°C/W	88.0°C/W
Multi-Layer PCB, JEDEC Standard Test Boards	73.2°C/W	66.6°C/W	63.5°C/W

TRANSISTOR COUNT

The transistor count for 844002 is: 2914



PACKAGE OUTLINE - G SUFFIX FOR 20 LEAD TSSOP

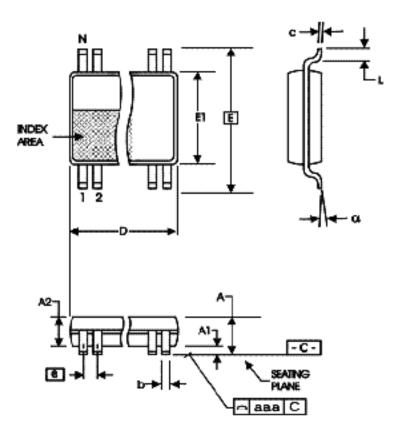


TABLE 8. PACKAGE DIMENSIONS

SYMBOL	Millin	meters		
STMBOL	MIN	MAX		
N	2	0		
A		1.20		
A1	0.05	0.15		
A2	0.80	1.05		
b	0.19	0.30		
С	0.09	0.20		
D	6.40	6.60		
E	6.40 E	BASIC		
E1	4.30	4.50		
е	0.65 E	BASIC		
L	0.45	0.75		
α	0°	8°		
aaa		0.10		

Reference Document: JEDEC Publication 95, MO-153



TABLE 9. ORDERING INFORMATION

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
844002AGLF	ICS844002AGL	20 Lead "Lead-Free" TSSOP	tube	0°C to 70°C
844002AGLFT	ICS844002AGL	20 Lead "Lead-Free" TSSOP	tape & reel	0°C to 70°C

NOTE: Parts that are ordered with an "LF" suffix to the part number are the Pb-Free configuration and are RoHS compliant.

REVISION HISTORY SHEET					
Rev	Table	Page	Description of Change	Date	
Α		6	Added Phase Noise Plots.	7/24/06	
Α		11	Power Consideraitons - corrected sentence after the Tj calculation.	1/19/07	
A	T1	1 2	Pin Assignment - corrected Pin 16 from V_{DD} to nc. Pin Description Table - deleted number 16 from VDD row and added row Pin 16 as a "nc".	9/28/07	
в	T3A, T3B T5A, T5B	3 5 7 8 8	Power Supply DC Characteristics Tables - changed VDDA max. from 3.465V to V AC Characteristics Tables - corrected NOTE 1. Corrected Output Rise/Fall Time Diagram. Updated Power Supply Filtering Technqiue paragraph text. Corrected Crystal Input Interface Diagram from 33/27p to 18/18p.	7/2/08	
В	Т9	14	Ordering Information - removed leaded devices. Updated data sheet format.	6/9/15	



IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use o any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners. **Contact Information**

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: <u>www.renesas.com/contact/</u>